# Development and novel applications of hybrid pixel detectors

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### CMS group

• High Energy Physics



### Photon science detector group

- Synchrotron Radiation
- Free-electron lasers
- Electron microscopes



### Photon science detector group

	MYTHEN II&III	EIGER	GOTTHARDI & II	JUNGFRAU	MÖNCH	AGIPD
1D/2D	Strip	Pixel	Strip	Pixel	Pixel	Pixel
Working Mechanism	Photon Counting	Photon Counting	Charge Integrating	Charge Integrating	Charge Integrating	Charge Integrating
Strip/Pixel size [µm]	50	75×75	25/50	75×75	25×25	200×200
Applications	Powder diffraction, energy- dispersive spectrometers , beam position.	Ptychography, coherent imaging, protein crystallography.	@ FLASH, main energy- dispersive detector for EU- XFEL.	Spectroscopic applications, high count rate applications at XFELs & synchrotrons.	(Biological) imaging & tomography, RIXS, spectroscopy, Laue diffraction.	Development for the EU- XFEL.



### Pixel detectors for synchrotrons

Their development at PSI started 20 years ago

 $\rightarrow$  State of the art: CCD systems  $\rightarrow$  bottleneck for science

Technology transferred from particle physics (CMS pixel detector at CERN)  $\rightarrow$  PILATUS was developed







PILATUS

- 15 years ago, DECTRIS spin off company was founded
  - $\rightarrow$  licensing of PILATUS, MYTHEN, EIGER.

Since then many PSI-technology detectors are contributing to science at every synchrotron <5 years ago: extension to electron microscopy started





Protein structure of SARS-COV-2 was solved with crystallography @ Shanghai Synchrotron in March 2020 using an EIGER 16M

### Outline

- Parallelism between CMS (HEP) and EIGER (Synchrotron)
  - Different subdetector components
  - Calibration
  - Rates
- Jungfrau specific implementation for FEL and synchrotron
- Electron microscopy
- Prospects for future developments



27 km circumference 4 TeV p beams

288 m circumference 2.4 GeV e beam Xrays 3eV – 45 keV





### CMS pixel BARREL detectors



Phase-1 upgrade @PSI 2017 operation in CMS 2017-2024

#### 1440 modules 66 M pixels



1856 modules 124 M pixels



Pixel size is 100x150 µm<sup>2</sup>

### HEP pixel detector requirements



- Temporary hit storage during trigger latency: readout according to the CMS Level 1 trigger selection
- Low noise
- Low in-time threshold
- Very high radiation tolerance design → charge particles
- Low material budget



### Pixel detectors at synchrotron



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### Synchrotron pixel detector requirements

- Energy range from a few to 25 keV
- Total frame readout
- Continuous beam, no trigger, high duty cycle
- High frame rate → tens of kHz
- Single photon sensitivity → low noise
- High dynamic range 1- 10<sup>4</sup> photons
- High count rate capability  $\rightarrow 10^{10}$  photons/cm<sup>2</sup>/s
- Spatial resolution <100 um
- High radiation tolerance  $\rightarrow \gamma$  rays, 30MRad

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75 um



- The energy is converted into electric charge
- About 3.6 eV to generate an e-h pair in silicon

#### In our usual applications:

• 300 um thick Si sensor

### Hybrid pixel detectors



#### Diced single chip full tests



#### Module tests





Full system test and calibration



### Hybrid pixel detectors



Sensor: particle interaction happens in sensor. Conversion to e/h pairs Readout chip: comparison to a threshold. Counting or PH sampled

#### Sensor



### Sensor choice for HEP



#### e<sup>-</sup> collection motivated by:

- Higher mobility : timing requirements
- Less charge trapping: radiation requirements
- Higher Lorentz angle: charge sharing

#### Ionization happens along the MIP track. dE/dx = 3.87 MeV/cm

$$\frac{dE/dx \cdot d}{I_0} = \frac{3.87 \cdot 10^6 \,\text{eV/cm} \cdot 0.03 \,\text{cm}}{3.62 \,\text{eV}} \approx 3.2 \cdot 10^4 \,\text{e}^-\text{h}^+\text{-pairs}$$

#### n<sup>+</sup> - in - n 100 x 150 um<sup>2</sup> Sensor thickness: 280 um





Spannagel et al., NIM A 2016 03 028

### Spatial resolution and Lorentz angle



- e<sup>-</sup> collection motivated by:
  - Higher Lorentz angle: charge sharing

CMS pixel resolution:

- 10.4 um transverse dir
- 20-45 um longitudinal direction depending on track angle



### Charge trapping



e<sup>-</sup> collection motivated by:

- Less charge trapping: radiation requirements
- Radiation damage causes defects in Si lattice
- Due to charge trapping: loss of signal charge
- Larger charge loss for larger (drift) depth for irradiated sensors
- Measured using inclined tracks
- Effect can be partially recovered by increasing the HV (450 V-800 V)

Affects the spatial resolution and needs to be taken into account in the reconstruction<sup>19</sup>

### Sensor: Si for X-rays

- Absorption of the X-rays in sensor: mainly photoelectric effect (<40 keV), 'pointlike'
- No bulk damage caused by Xrays: hole collection
- Leakage current increase with dose expected
- •The sensor (320um thick) 'protects' the readout chip up to 8 keV X-rays







### Readout chip



### Readout chip characteristics

Layer 2-4 psi46dig Layer 1 PROC 600 (optimed data rate sending 2x2 clusters)





property psi46dig		EIGER	
technology IBM 250 nm		UMC 250 nm	
	Rad. tol. Design>250 Mrad	Rad. tol. Design≈30 Mrad	
pixel array	80×52=4160 pixels	256×256=65536 pixels	
pixel size	$100 \times 150 \ \mu m^2$	$75 \times 75 \ \mu m^2$	
count rate	$1.2 \cdot 10^8$ hits/cm <sup>2</sup> /s	$1.8 \cdot 10^{10}$ hits/cm <sup>2</sup> /s	
data rate	160 Mb/s	6 Gb/s	
analog power	11 $\mu$ W/pixel	10 $\mu$ W/pixel	
digital power	17 $\mu$ W/pixel	0.2 W (static periphery)	
total static power	0.12 W	0.83 W	

### Readout chip analog part



property	psi46dig	EIGER	
output	event pulse height with	event counts with	
	timestamped hits	configurable integration time	
	100 kHz	22kHz	

### Readout electronics



### CMS: low material budget



- Maintaining low material budget → CO<sub>2</sub> cooling with small pipes (-23°C)
- Data out of L1 trigger: 30-100 GB/s depending on Pile up

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-2

CERN-CMS-NOTE-2020-005

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### EIGER: Very high frame rate



2x10 Gb/s Ethernet connections are the bottleneck when running at maximum framerate

Thanks to large memory on board, we can buffer images

6 FPGAs per module 8 GB DDR2 per module



9M detector, up to 360Gb/s

0.5M single module, 20Gb/s

4 us dead time between frames Time covered : 1.4 s

Water cooling at 20°C, mainly for FPGAs

Dynamic range (bit)	Continuous frame rate @10 Gb (kHz)	Buffered max frame rate (kHz)	Images stored	
4	10.2	22	30000	
8	5.12	11	15000	
12	2.56	6	7600	
32	2 kHz internal	0.8	Online sum	26

- Parallelism between CMS (HEP) and EIGER (Synchrotron)
  - Different subdetector components
  - Calibration
  - Rates
- Jungfrau specific implementation for FEL and synchrotron
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### Calibration: threshold scans



### CMS threshold and noise



### EIGER threshold and noise

- Single photon counters: compare the signal to threshold
- Threshold is normally set to 50% beam energy to optimize for charge sharing between pixels
- Low noise <100 e<sup>-</sup> RMS. Energy resolution 360-700 eV RMS at 3-15 keV
- Threshold can be set at > 3keV → beam energy optimal >6keV



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### CMS hit rate and efficiency

A	Pixel hit rate	Fluence	Dose
	$[MHz/cm^2]$	$[10^{15} n_{eq}/cm^2]$	[Mrad]
BPIX L1	580	2.2	100
BPIX L2	120	0.9	47
BPIX L3	58	0.4	22
BPIX L4	32	0.3	13
FPIX inner rings	56-260	0.4-2.0	21-106
FPIX outer rings	30-75	0.3-0.5	13-28

From simulation Instantaneous luminosity 2 10<sup>34</sup> cm<sup>-2</sup> s<sup>-1</sup> Integrated luminosity 300 fb<sup>-1</sup>

- Inefficiency <3 % till end run2
- PROC 600 designed to stand 600 MHz/cm2



#### MS beamline

### EIGER count rate characterization

**PILE UP** 







Paralizable counter model:

$$N_{det} = N_{inc} \cdot e^{-N_{inc} \cdot \tau}$$

Effect can be partially corrected for

- Dependence on gain settings
- Correction only possible on the ascending part
- τ = 200-700 ns

### Protein crystallography



High rate capability: 1M counts/pix/s







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### Swiss Light Source and SwissFEL



Higher brilliance than synchrotron and faster dynamics

Xrays 250 eV - 12.4 keV (7 to 1 Å)

#### Synchrotron source:

- Semi-continuous, a bunch every 2 ns
- "Weak" bunches  $\rightarrow 10^3$  photons/pulse
- Bunch length is 20 ps

#### FEL:

- 100 Hz repetition rate
- Fewer intense bunches  $\rightarrow 10^{11}$  photons/pulse
- All photons in the bunch coming at once (1-60 fs pulse lengths)

### CI detector + dynamic gain switching



- •For the detector the main challenges are:
  - Single photon resolution
  - Dynamic range of 10<sup>4</sup> 12 keV photons per acquisition
- In exposure 'dynamic gain switching' is our solution



### Gain switching and noise





 Dynamic range is 10<sup>4</sup> 12 keV photons



- Noise < statistical limit
- Single photon resolution at 2keV
- JF gives single photon counting equivalent data quality
- Large dynamic range → high
  rate capability
  - 1000 photons @ 12 keV
  - 12000 photons @ 1 keV

### JUNGFRAU readout: FEL vs synchrotrons

	Integration t [µs]	Frame rate [Hz]	Data rate/module [Gbit/s]
SwissFEL	10	100	0.8
Synchrotron	400	2.2 k	18



New readout board (2019)



- Integrated charge from dark images: sensitive to leakage current
- The longer the exposure, the higher the integrated dark image charge
- Cooling of the sensor necessary (down to -12°C)

### Advantages of JF at synchrotrons

**FIGER** 'like

threshold

140

100

60

- EIGER can loose small diffraction peaks between pixels in the case the events is at the corner of 4 pixels → JF provides better pixel uniformity
- EIGER is limited by pile up → JF has much higher rate capability, fast data acquisition with higher transmission possible
- EIGER has a lower threshold limit at 3 keV (ideal for 6keV beam). JF tested at synchrotrons at 3.75 keV



#### Pencil beam scan, 20 keV





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### EIGER in electron microscopy

- PEEM Photo Emission Electron Microscopy - Imaging
  - ELMITEC, SIM Beamline SLS

vacuum

20keV Electrons

Sample

Chamber



Prof. Jan Pieter Abrahams C-CINA/PSI







- For energies <=100 keV, hybrid pixels are an "ideal detector"</li>
- At higher energies, EIGER is appealing thanks to frame rate: scanning/rotation techniques, imaging single electrons, reducing sample drift

### EIGER as a detector for low energy electrons



### Low energy electron interaction



#### Completely rad hard for 8-20 keV e<sup>-</sup>



• e<sup>-</sup> interaction:

- lose energy due to multiple collisions with atomic electrons
- Deposit energy in multiple points due to multiple scattering
- Al layer can be etched away
- e<sup>-</sup> lose part of their energy in Si backplane



### Thin entrance window sensors



**FBK** 



Tinti el al., IUCrJ 2018 5(2)



- High-Z sensors for 300 keV electrons
- Smaller pixels (same sensor height) : ONLY useful with TIMING info → TIMEPIX
- THIN MONOLITHIC pixel detectors for E>100 keV but RADIATION HARNESS

- Parallelism between CMS (HEP) and EIGER (Synchrotron)
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### R&D fur future HEP pixel detectors



Exploit potential offered by depleted monolithic pixel detector technology:

- less material  $\rightarrow$  less multiple scattering
- smaller pixels  $\rightarrow$  improved spatial resolution
- lower costs  $\rightarrow$  large area pixel detector

High radiation tolerance extension needs R&D studies

### MÖNCH

**25 x 25**  $\mu$ m<sup>2</sup> pixel size

Small pixels + charge sharing  $\rightarrow$  spatial resolution Low noise  $\rightarrow$  low energy





- Area 1x1 cm<sup>2</sup>
- Charge integrating
- Pixel architecture optimized for low noise
  - No dynamic gain switching
- 2-3 kHz frame rate (10 Gb port)
  - Up to 6 kHz by design





Single photon resolution down to about 800 eV (220e-)



- 200nm thin backplane sensors are being tested now for JUNGFRAU and MOENCH
- Extend the transmission> 600eV and in the ultra violet region



### Low Gain Avalanche Detectors (LGAD) Collaboration



Charge multiplication Amplify signal in the sensor

Moderate gain (5-20) No dark counts Collaboration with FBK to design optimal sensors

Andrae et al, JSR 2019 26

Same technology used in HEP to improve timing

of the scurves for different fluorescence at bias voltage -110 V

counts [a.u.] In 3.3 keV Ca 3.7 keV Ti 4.5 keV Cr 5.4 keV Fe 6.4 keV Cu 8.1 keV Ge 9.9 keV Zr 15.8 keV Mo 17.5 keV 0.5 0 300 350 400 450 500 550 threshold [DAC]

Only strip detectors tested so far, pixel planned in the future, but fill factor and segmentation need to be improved

By amplifying the signal already in the sensor, one can detect energies that are not possible with a standard sensor: >3 keV can be easily seen vs 8 keV of the standard detector



150 µm strip-pitch, 50 µm thick on substrate, 4 mm long High input capacitance (~2.5 pF)  $\rightarrow$  higher noise Region without multiplication between strips: fill factor ~45%

## R&D towards pixelated LGADs with thin entrance window: goal extend EIGER use to 1keV

### High-Z sensors for higher energies



- Extend efficiency for higher energy X-rays
- Ideally use for electron microscopy >100keV
- Extensive R&D program needed to achieve same quality as Si

#### Pencil beam scan of the charge collected by a single pixel (20keV):



### Conclusions

#### • HEP:

- Operation of phase I CMS
- Involvement in HL-LHC forward region acceptance extension TEPX Phase II (2027)
- Extension of radiation tolerance and monolithic
- Synchrotron:
  - Maintaining single photon counting technology as advantages of data reduction compared to charge integrating detectors
  - $\circ$  count rate capability (1M counts/pix/s) → 20 M counts/pix/s in view of SLS2 (2024)
  - Extension of use >1keV through special sensors

#### • FEL:

- Large data handling to be further developed
- Even lower noise readout chips for single photon resolution at >700eV (90eV) with special sensors
- Electron microscopy:
  - High count rates in diffraction require use of charge integrating technology
  - Monolithic pixel detectors to limit multiple scattering

#### SUCH A COMPREHENSIVE RESEARCH PLAN CAN BE DEVELOPED ONLY IN A RESEARCH CENTER 53

### Spatial interpolation with MÖNCH



Gold on Silicon sample, MS beamline (SLS), 8keV, with MÖNCH

### Spatial interpolation with MÖNCH



Gold on Silicon sample, MS beamline (SLS), 8keV, with MÖNCH



### Thanks for the attention!

### Threshold energy calibration

Tinti et al., Performance of the EIGER single photon counting detector, JINST 10 C03011 (2015)



$$RMS_{tot} = \sqrt{RMS_{noise}^2 + RMS_{th}^2}$$

- Noise RMS: 100 200 e- depending on preamp gain:
- 360 720 eV Noise RMS

#### **Gain calibration**

Calibrated conversion from ADC units to deposited charge units:



Cal signal calibration



Gain calibration is dependent from:

- temperature
- radiation
- analog voltage setting

Calibration similar to the one required by charge integrating detectors with analog readout for photon science 

#### Gain calibration as function of occupancy



- Temperature sensor on the readout chip. Calibration performed offline.
- Higher occupancy → higher digital activity → higher temperature
- · During fill, the temperature decays exponentially following instantaneous luminosity
- Effect visible in the cluster charge: Occupancy dependent gain calibration

# Single Photon Counting vs Charge integrating detectors

#### SINGLE PHOTON COUNTERS:

- Count a photon every time the signal is above a threshold
- Dynamic range limited by counter depth
- Ideal signal over noise ratio
- The threshold allows for fluorescence rejection
- Time required by the CHAIRGE INTEGRATING er DETECTORS d ~100ns →
- Sytechate on arge during acquisition window
- Necessary at FELs
- No minimum photon energy, but the noise is measured
- For monochromatic beam,





### Analog functionality in a pixel cell





Pixel detector development at the Paul Scherrer Institut (CH):

- High Energy Physics
- Synchrotron Radiation
- Free-electron lasers
- Electron microscopes

### Leakage current

Phase-1 Pixel - Full depletion voltage vs days



- Radiation effects due to surface sensor damage
- Increase in i\_leak proportional to fluence
- Depends on T and annealing
- Expect to collect 300 fb<sup>-1</sup> in LHC Run 3 (2021-2024)



### Threshold dispersion: threshold equalization



### CMS hit rate

Layer radius	3 cm	7 cm	11 cm	16 cm
Pixel fluence [MHz/cm <sup>2</sup> ]	520	119	52	27
Hits / trigger / module	190	40	18	8.4
MBit/link/sec	435	118	66	45

#### From simulation

- Inefficiency <3 % till end run2
- PROC 600 designed to stand 600 MHz/cm2

